

Small Plastic Package, Dual SPDT Analog Switch

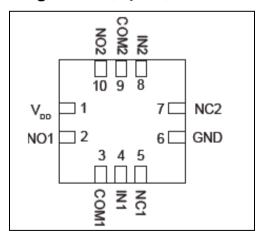
Features

- → CMOS Technology for Bus and Analog Applications
- \rightarrow Low On-Resistance: 0.45 Ω
- → Wide V_{DD} Range: 1.8V to 4.2V
- → Rail-to-Rail Signal Range
- → High Off Isolation: -83dB @ 100kHz
- → Crosstalk Rejection Reduces Signal Distortion: -108dB @ 100kHz
- → Break-Before-Make Switching
- → Extended Industrial Temperature Range: -40°C to 85°C
- \rightarrow ESD protection : 4kV(HBM)
- → Packaging (Pb-free & Green):
 - -10-pin UQFN (ZM), 1.4mm x 1.8mm

Applications

- → Cell Phones
- → PDAs
- → MP3 Players
- → Portable Instrumentation
- → Computer Peripherals
- → Speaker Headset Switching
- → Power Routing
- → Relay Replacement
- → Audio and Video Signal Routing
- → PCMCIA Cards
- **→** Modems

Pin Configuration (Top view)

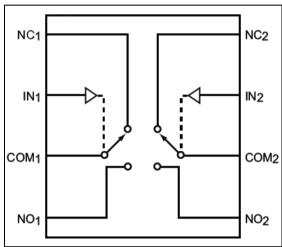


Description

PI3A223 is a dual fast single-pole double throw (SPDT) CMOS switch. It can be used as an analog switch or as a low-delay bus switch. Specified over a wide operating power supply voltage, 1.8V to 4.2V, the PI3A223 has an On-Resistance of 0.45Ω at +4.2V.

Break-before-make switching prevents both switches being enabled simultaneously. This eliminates signal disruption during switching.

Block Diagram



Pin Description

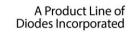
Pin#	Name	Description
1	V_{DD}	Positive Power Supply
2	NO1	Data Port (Normally open)
3	COM1	Common Output / Data Port
4	IN1	Logic Control
5	NC1	Data Port (Normally closed)
6	GND	Ground
7	NC2	Data Port (Normally closed)
8	IN2	Logic Control
9	COM2	Common Output / Data Port
10	NO2	Data Port (Normally open)

Function Table

Logic Input (IN _X)	Function
0	NC_X Connected to COM_X
1	NO _X Connected to COM _X

Note: x = 1 or 2







Maximum Ratings

Storage Temperature	
Ambient Temperature with Power Applied	40°C to +85°C
Supply Voltage V _{DD}	0.5Vto +4.6V
Control Input Voltage V _{INx}	0Vto +4.6V
DC Input Voltage V _{INPUT}	0.5Vto +4.6V
Continuous Current NO_NC_COM	±300mA
Peak Current NO_NC_COM_	
(pulsed at 1ms 50% duty cycle)	±400mA
Peak Current NO_NC_COM_	
(pulsed at 1ms 10% duty cycle)	±500mA
ESD(HBM)	4kV

Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

The input and output negative voltage ratings may be exceeded if the input and output diode current ratings are observed.

Control input must be held HIGH or LOW; it must not float.

Recommended Operating Conditions

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V_{DD}	Operating Voltage	=	1.8	-	4.2	V
$V_{\rm IN}$	Control Input Voltage	=	0	-	$V_{ m DD}$	V
V _{INPUT}	Switch Input Voltage	=	-0.3	-	4.2	V
T_{A}	Operating Temperature	-	-40	25	85	°C
t_r, t_f	Input Rise and Fall Time	-	0	-	10	ns/V

DC Electrical Characteristics

+3.0V Supply (V_{DD} = 2.7V to 3.6V, V_{IH} =+1.6V, V_{IL} =+0.4V, T_A = -40 °C to 85 °C, unless otherwise noted. Typical values are at 3.0V and +25 °C.)

Parameter	Symbol	Test Conditions	TEMP	Min.	Тур.	Max.	Units
ANALOG SWITCH							
Analog Signal Range	$egin{array}{c} egin{array}{c} egin{array}{c} V_{ m NO}, \ V_{ m COM} \end{array}$	-	-40 °C to 85 °C	0	-	V_{DD}	V
On-Resistance	R_{ON}	$V_{DD} = 2.7V$, $I_{COM} = 100mA$, V_{NO} or	+25°C	-	0.55	0.9	Ω
On-Resistance	KON	V _{NC} =1V, Test Circuit 1	-40 °C to 85 °C	-	0.55	1	
On-Resistance Match	ΔR_{ON}	$V_{DD} = 2.7V$, $I_{COM} = 100$ mA, V_{NO} or	+25°C	ı	0.05	0.22	Ω
Between Channels		V _{NC} =1V, Test Circuit 1	-40 °C to 85 °C	ı	0.05	0.25	
On-Resistance	R_{ONF}	$V_{DD} = 2.7V$, $I_{COM} = 100$ mA, V_{NO} or	+25°C	-	0.1	0.22	Ω
Flatness		$V_{NC} = 1V, 2.5V, Test Circuit 1$	-40 °C to 85 °C	-	0.1	0.26	
Source Off Leakage Current	I _{OFF (NO)} or	$V_{DD}=3.6V$, V_{NO} or $V_{NC}=3.3V/0.3V$, $V_{COM}=0.3V/3.3V$	-40 °C to 85 °C	-	-	1	
	$I_{OFF (NC)}$ $I_{NC(ON)}$,						μA
Channel On Leakage Current	$I_{NO(ON)}, I_{COM}$	$V_{DD} = 3.6V$, V_{NO} or $V_{NC} = 3V/0.3V$, $V_{COM} = 3V/0.3V$, or floating	-40 °C to 85 °C	-	-	1	
	(ON)	ole v, veolvi e v, ole v, ol mouning					
DIGITAL INPUTS		T			1		I
Input Logic High	V_{IH}	-	-40 °C to 85 °C	1.2	-	-	v
Input Logic Low	$ m V_{IL}$	-	-40 °C to 85 °C	-	-	0.5	,
IN Input Leakage Current	$I_{ m IN}$	$V_{DD} = 2.7V, V_{IN} = 0 \text{ or } 2.7V$	-40 °C to 85 °C	-	-	1	μA
DYNAMIC CHARAC	CTERISTICS		l		I.		I.
Turn-On Time	t_{ON}	V _{IH} =1.5V, V _{IL} =0V, See Test Circuit Figure 2.	+25°C	-	16	-	ns
Turn-Off Time	t _{OFF}	V _{IH} =1.5V, V _{IL} =0V,	+25°C	_	60	_	ns
	OFF	See Test Circuit Figure 2.					110
Break-Before-Make	t_{D}	$V_{IH}=1.5V, V_{IL}=0V,$	+25°C	-	10	-	ns





Parameter	Symbol	Test Conditions	Test Conditions		Min.	Тур.	Max.	Units
Delay		See Test Circuit Figure 3.						
	$V_{BIAS}=1.5V, V_{IN}=0dBm,$		100kHz	+25°C	-	-81	-	
COM-NC/NO and NC-NO Isolations	${ m O_{ISO}}$	V _{IH} =1.5V, V _{IL} =0V. See Test Circuit Figure 4 &	1MHz	+25°C	-	-61	-	dB
		Figure 5.	10MHz	+25°C	-	-39	-	
		$V_{BIAS} = 1.5V,$	100kHz	+25°C	-	-108	-	
Channel-to-Channel Crosstalk	X_{TALKD}	V _{DD} =0dBm, V _{IH} =1.5V, V _{IL} =0V See Test Circuit	1MHz	+25°C	-	-110	-	dB
		Figure 6.	10MHz	+25°C	-	-90	-	
3dB Bandwidth	$ m f_{3dB}$	$V_{BIAS} = 1.5V$, $V_{IN} = 0$ dBm, $V_{IH} = 1.5V$, $V_{IL} = 0V$. See Test Circuit Figure 7.		+25°C	-	79	-	MHz
Charge Injection Select Input to Common I/O	Q	$V_{IN} = GND, R_S = 0, C$ V_{IH} =1.5V, V_{IL} =0V See Test Circuit Figure 8.	$V_{IN} = GND, R_S = 0, C_L = 1nF, V_{IH}=1.5V, V_{IL}=0V$		-	35	-	pC

+4.2V Supply ($V_{DD} = 4.2V$, $T_A = -40$ °C to 85 °C, unless otherwise noted. Typical values are at 4.2V and +25 °C.)

Parameter	Symbol	Test Conditions		TEMP	Min.	Typ.	Max.	Units	
ANALOG SWITCH	ı v			l			I.	ı	
Analog Signal Range	$V_{NO}, V_{NC}, \ V_{COM}$	-		-40 °C to 85 °C	0	-	V_{DD}	V	
On-Resistance	R _{ON}	$V_{DD} = 4.2V$, $I_{COM} = 100$ m. $V_{NC} = 1V$, Test Circuit 1	A, V_{NO} or	+25°C -40 °C to 85 °C	-	0.45 0.45	0.75 0.85	Ω	
On-Resistance Match Between Channels	$\Delta R_{ m ON}$	$V_{DD} = 4.2V$, $I_{COM} = 100m$ $V_{NC} = 1V$, Test Circuit 1	A, V _{NO} or	+25°C -40 °C to 85 °C	-	0.05	0.18	Ω	
On-Resistance Flatness	R _{ONF}	$V_{DD} = 4.2V, I_{COM} = 100mA$ $V_{NC} = 1V, 2.5V, Test Circ$		+25°C -40 °C to 85 °C	-	0.1	0.22	Ω	
Source Off Leakage Current	$I_{OFF(NO)}$ or $I_{OFF(NC)}$	V_{DD} = 4.2V, V_{NO} or 3.3V/0.3V, V_{COM} = 0.3V/3	$V_{NC} =$	-40 °C to 85 °C	-	_	1	μA	
Channel On Leakage Current	$I_{NC(ON)},$ $I_{NO(ON)},$ I_{COM} (ON)	$V_{DD} = 4.2V$, V_{NO} or $V_{NC} = 3V/0.3V$, $V_{CO}M = 3V/0.3V$, or floating		-40 °C to 85 °C	-	-	1	μΑ	
DIGITAL INPUTS	, , , , , , , , , , , , , , , , , , , ,	1				•			
Input Logic High	V_{IH}	-		-40 °C to 85 °C	1.2	-	-	17	
Input Logic Low	$V_{ m IL}$	-		-40 °C to 85 °C	-	-	0.5	V	
IN Input Leakage Current	I_{IN}	$V_{DD} = 4.2V, V_{IN} = 0 \text{ or } 4.2V$		-40 °C to 85 °C	-	-	1	μA	
DYNAMIC CHARAC	CTERISTICS								
Turn-On Time	t _{ON}	V _{IH} =3V, V _{IL} =0V, See Test Circuit Figure 2.			1	13	-	ns	
Turn-Off Time	$t_{ m OFF}$	V _{IH} =3V, V _{IL} =0V, See Test Circuit Figure 2.		+25°C	-	38	-	ns	
Break-Before-Make Delay	t_{D}	V _{IH} =3V, V _{IL} =0V, See Test Circuit Figure 3.		+25°C	-	8	-	ns	
		$V_{BIAS} = 2.1V$,	100kHz	+25°C	-	-83	-		
COM-NC/NO and NC-NO Isolations	$O_{\rm ISO}$	V _{IN} =0dBm, V _{IH} =3V, V _{IL} =0V. See Test Circuit	1MHz	+25°C	-	-61	-	dB	
		Figure 4 & Figure 5.	10MHz	+25°C	-	-39	-		
Channel-to-channel	Channel-to-channel X_{TALK} $V_{BIAS} = 2.1V$, $V_{IN} = 0$ dBm, $V_{IH} = 3V$,		100kHz	+25°C	-	-108	-	dB	
Crosstalk		V _{IL} =0V See Test Circuit	1MHz	+25°C	-	-110	-	uD	







Parameter	Symbol	Test Conditions	Test Conditions		Min.	Typ.	Max.	Units
		Figure 6.	10MHz	+25°C	-	-90	-	
3dB Bandwidth	f_{3dB}	$V_{BIAS} = 2.1V$, V_{IN} =0dBm, V_{IL} =0V. See Test Circuit F		+25°C	-	84	-	MHz
Charge Injection Select Input to Common I/O	Q	$V_{IN} = GND, R_S = 0, C_L = 1nF,$ $V_{IH}=3V, V_{IL}=0V$ See Test Circuit Figure 8.		+25°C	-	50	-	pC
POWER REQUIREMENTS						•		
Power Supply Range	$V_{ m DD}$	-		-40 °C to 85 °C	1.8	-	4.2	V
Power Supply Current	I_{CC}	V_{DD} =4.2V, V_{IN} =0V or V_{DD})	-40 °C to 85 °C	-	_	1	μΑ

Capacitance

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Units
NC Off Capacitance	$C_{NC (OFF)}$	f = 1MHz, See Test Circuit Figure 9.	ı	20	ı	
NO Off Capacitance	C _{NO (OFF)}	f = 1MHz, See Test Circuit Figure 9.	-	20	1	pF
NC On Capacitance	$C_{NC (ON)}$	f = 1MHz, See Test Circuit Figure 10.	-	55	1	þГ
NO On Capacitance	$C_{NO (ON)}$	f = 1MHz, See Test Circuit Figure 10.	ı	55	- 1	



Test Circuits and Timing Diagrams

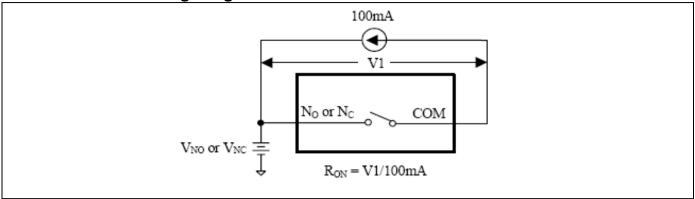


Figure 1. On Resistance

Notes:

1. Unused input (NC or NO) must be grounded.

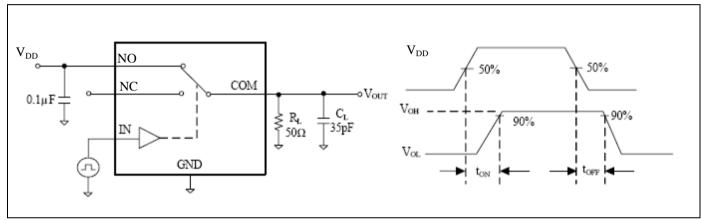


Figure 2. Switching Times

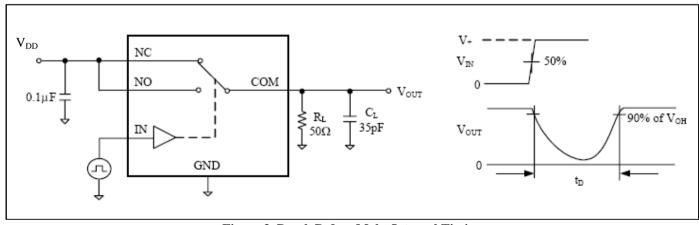


Figure 3. Break Before Make Interval Timing



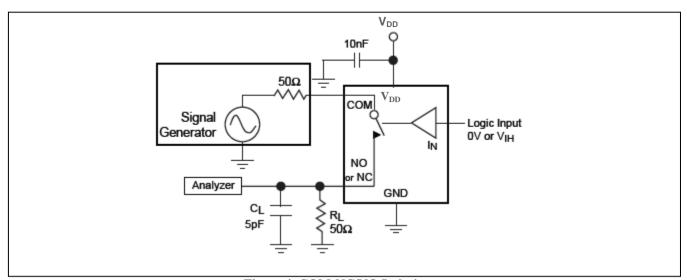


Figure 4. COM-NC/NO Isolation

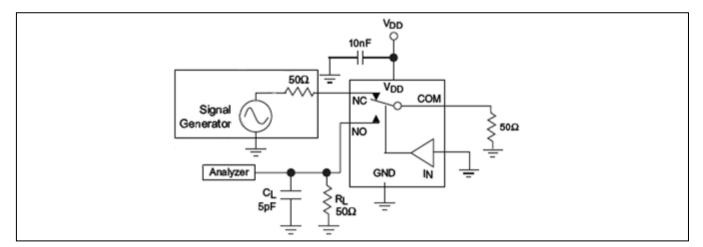


Figure 5. NC-NO Isolation



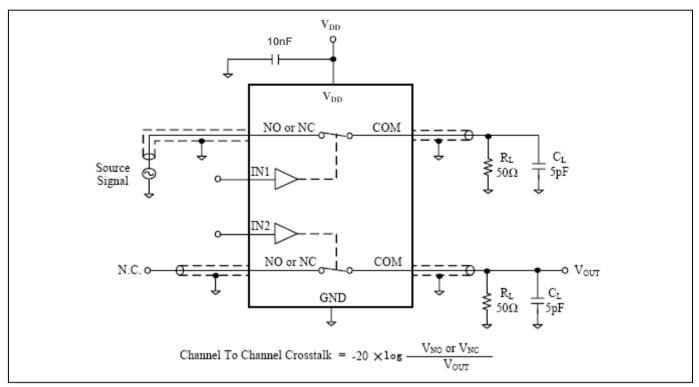


Figure 6. Channel-to-Channel Crosstalk

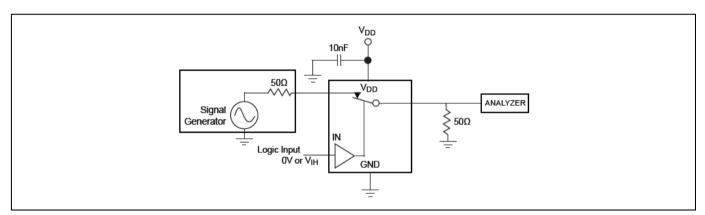


Figure 7. Bandwidth

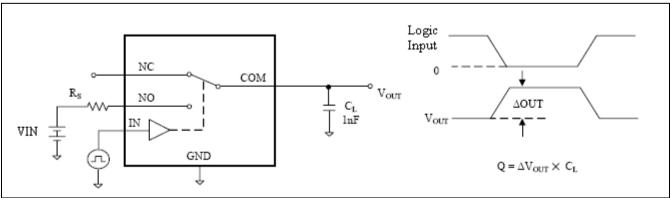


Figure 8. Charge Injection



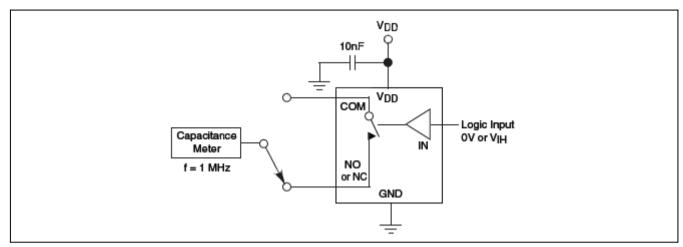


Figure 9. Channel Off Capacitance

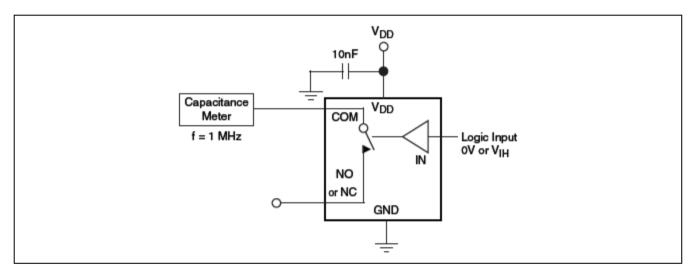
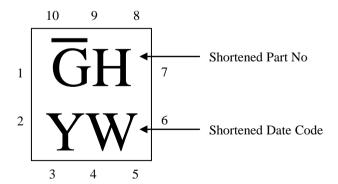


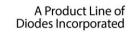
Figure 10. Channel On Capacitance

Part Marking

ZM Package



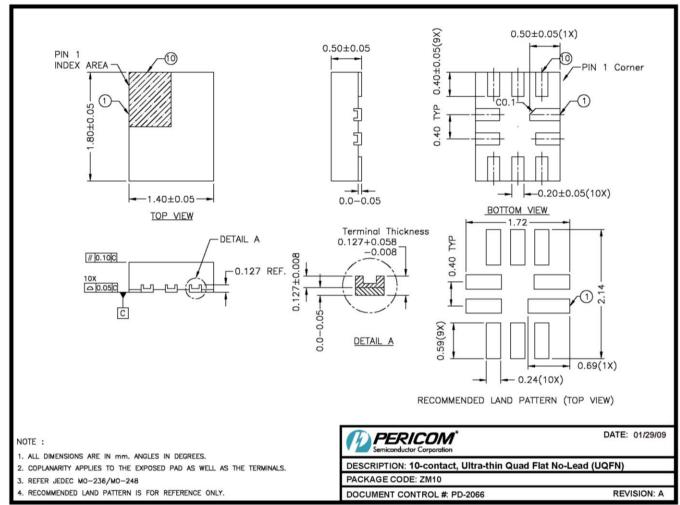






Packaging Mechanical

10-UQFN (ZM)



09-0072

For latest package info.

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Ordering Information

Part Number	Packaging Code	Package Description
PI3A223ZMEX	ZM	10-Contact, Ultra-thin Quad Flat No-Lead (UQFN)

Notes:

- EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- Thermal characteristics can be found on the company web site at www.diodes.com/design/support/packaging/
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- X suffix = Tape/Reel





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